

What is claimed is:

1. A method of creating regions of different amounts of conductivity on the surface of a solar cell comprising:  
performing a first blanket doping using a first dopant on a surface of said solar cell, such that said surface comprises a doped region;  
depositing conductors onto said surface of said solar cell after said first blanket doping, each pair of said conductors forming a space between; and  
performing a second blanket doping using a second dopant on said surface after said depositing said conductors, wherein said first dopant and said second dopant comprise opposite conductivities and whereby said second dopant is implanted through said space between said conductors and wherein said doped region retains the conductivity of said first dopant.
2. The method of claim 1, wherein said first blanket doping is performed via furnace diffusion.
3. The method of claim 1, wherein said first blanket doping and said second blanket doping are performed via ion implantation.
4. The method of claim 1, wherein said first blanket doping is performed via plasma doping.
5. The method of claim 1, further comprising performing an activation step subsequent said first blanket doping of said first dopant.
6. The method of claim 5, wherein said activation step is performed prior to said depositing of said conductors.
7. The method of claim 5, wherein said activation step is performed subsequent to said depositing of said conductors.
8. The method of claim 1, further comprising depositing an anti-reflective coating onto said surface of said solar cell.

9. The method of claim 8, wherein said anti-reflective coating is deposited prior to depositing said conductors.

10. The method of claim 8, wherein said anti-reflective coating is deposited subsequent to depositing said conductors.

11. The method of claim 10, wherein said anti-reflective coating is deposited subsequent to said second blanket doping.

12. The method of claim 1, wherein said first dopant comprises a Group III element.

13. The method of claim 1, wherein said first dopant comprises a Group V element.

14. A method of doping a substrate, comprising  
depositing conductors onto a surface of said substrate; and  
performing an ion implantation on said surface using a dopant after depositing said conductors, whereby said conductors prevent said dopant from implanting said substrate beneath said conductors.

15. The method of claim 14, wherein said substrate has an initial conductivity prior to said depositing of said conductors.

16. The method of claim 15, wherein said dopant has a conductivity opposite of said initial conductivity of said substrate.

17. The method of claim 16, wherein said dopant comprises a Group III element.

18. The method of claim 16 wherein said dopant comprises a Group V element.

19. The method of claim 14, wherein said substrate comprises a solar cell.

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